

[TABLE 1]

ITEMS		FIRST AMORPHOUS SEMICONDUCTOR FILM	SECOND AMORPHOUS SEMICONDUCTOR FILM
SiH <sub>4</sub> FLOW AMOUNT	[sccm]	50~95	100
GeH <sub>4</sub> (H <sub>2</sub> -BASE 10%) FLOW AMOUNT	[sccm]	50~5	0
RF POWER	[W/cm <sup>2</sup> ]	0.35	←
PULSE FREQUENCY	[KHz]	10	←
DUTY	[%]	30	←
PRESSURE	[Pa]	33.25	←
SUBSTRATE TEMPERATURE (T <sub>sub</sub> )	[°C]	300	←
ELECTRODE GAP (GAP)	[mm]	35	←

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